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Joe McKinney Mur Attorney Reg. No.:		1		Dated:	July 28, 2005
BIRCH, STEWART 8110 Gatehouse R		ł & BIRCH, LL	.P		
Suite 100 East P.O. Box 747 Falls Church, Virgii (703) 205-8026	nia 22040-0)747			



Docket No.: 0941-0924P

(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Min-hung Lee et al.

Application No.: 10/791,816

Confirmation No.: 003667

Filed: March 4, 2004

Art Unit: 2811

For: STRAINED SILICON CARBON ALLOY

MOSFET STRUCTURE AND FABRICATION

METHOD THEREOF

Examiner: S. Hu

AMENDMENT IN RESPONSE TO NON-FINAL OFFICE ACTION

MS Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

INTRODUCTORY COMMENTS

In reply to the Office Action dated April 28, 2005, the following amendments and remarks are respectfully submitted in connection with the above-identified application.

This reply includes:

Amendments to the Specification;

Amendments to the Claims; and

Remarks.